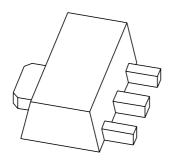
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# BST60; BST61; BST62 PNP Darlington transistors

Product data sheet Supersedes data of 2001 Feb 20

2004 Dec 09



# **PNP Darlington transistors**

# **BST60**; **BST61**; **BST62**

### **FEATURES**

- High current (max. 0.5 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

### **APPLICATIONS**

- Industrial switching applications such as:
  - Print hammer
  - Solenoid
  - Relay and lamp driving.

### **DESCRIPTION**

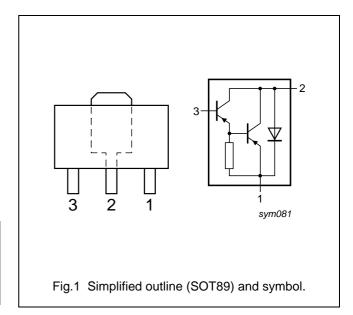
PNP Darlington transistor in a SOT89 plastic package. NPN complements: BST50, BST51 and BST52.

### **MARKING**

TYPE NUMBER	MARKING CODE
BST60	BS1
BST61	BS2
BST62	BS3

### **PINNING**

PIN	DESCRIPTION
1	emitter
2	collector
3	base



### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE			
TIPE NOMBER	NAME	DESCRIPTION	VERSION	
BST60	SC-62	plastic surface mounted package; collector pad for good heat	SOT89	
BST61		transfer; 3 leads		
BST62				

# PNP Darlington transistors

BST60; BST61; BST62

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BST60		_	-60	V
	BST61		_	-80	V
	BST62		_	-90	V
V <sub>CES</sub>	collector-emitter voltage	V <sub>BE</sub> = 0 V			
	BST60		_	-45	V
	BST61		_	-60	V
	BST62		_	-80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)		_	-1	А
I <sub>CM</sub>	peak collector current		_	-2	А
I <sub>B</sub>	base current (DC)		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	1.3	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

### Note

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	96	K/W
$R_{th(j-s)}$	thermal resistance from junction to soldering point		16	K/W

### Note

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

<sup>1.</sup> Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

# PNP Darlington transistors

BST60; BST61; BST62

### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS		TYP.	MAX.	UNIT
I <sub>CES</sub>	collector-emitter cut-off current					
	BST60	$V_{BE} = 0 \text{ V}; V_{CE} = -45 \text{ V}$	_	_	-50	nA
	BST61	$V_{BE} = 0 \text{ V}; V_{CE} = -60 \text{ V}$	_	_	-50	nA
	BST62	$V_{BE} = 0 \text{ V}; V_{CE} = -80 \text{ V}$	_	_	-50	nA
I <sub>EBO</sub>	emitter-base cut-off current	$I_C = 0 \text{ A}; V_{EB} = -4 \text{ V}$	_	_	-50	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -10 V; note 1; see Fig.2				
		$I_{C} = -150 \text{ mA}$	1000	_	_	
		I <sub>C</sub> = −500 mA	2000	_	_	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -500 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-1.3	V
	voltage	$I_C = -500 \text{ mA}; I_B = -0.5 \text{ mA};$ $T_j = 150 \text{ °C}$	_	_	-1.3	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-1.9	V
f <sub>T</sub>	transition frequency	$I_C = -500 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	_	200	_	MHz
Switching ti	Switching times (between 10% and 90% levels); (see Fig.3)					
t <sub>on</sub>	turn-on time	$I_{Con} = -500 \text{ mA}; I_{Bon} = -0.5 \text{ mA};$	_	500	_	ns
t <sub>off</sub>	turn-off time	I <sub>Boff</sub> = 0.5 mA	_	700	_	ns

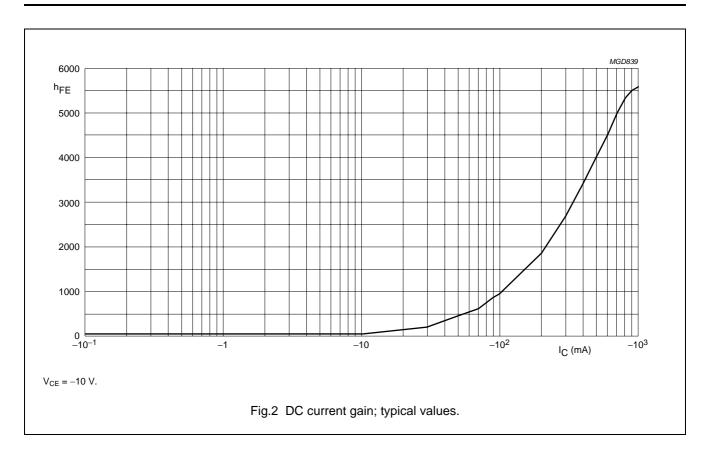
### Note

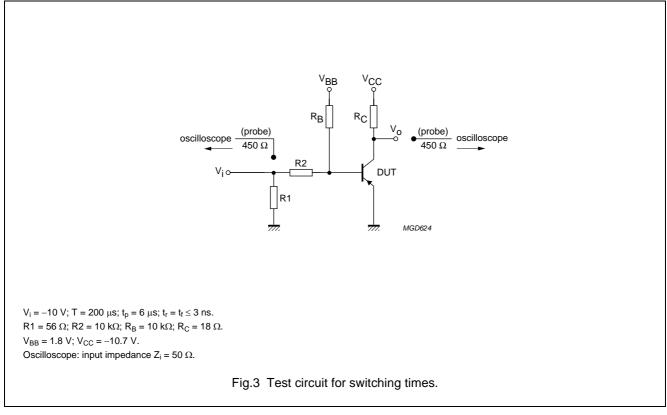
1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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# PNP Darlington transistors

# BST60; BST61; BST62





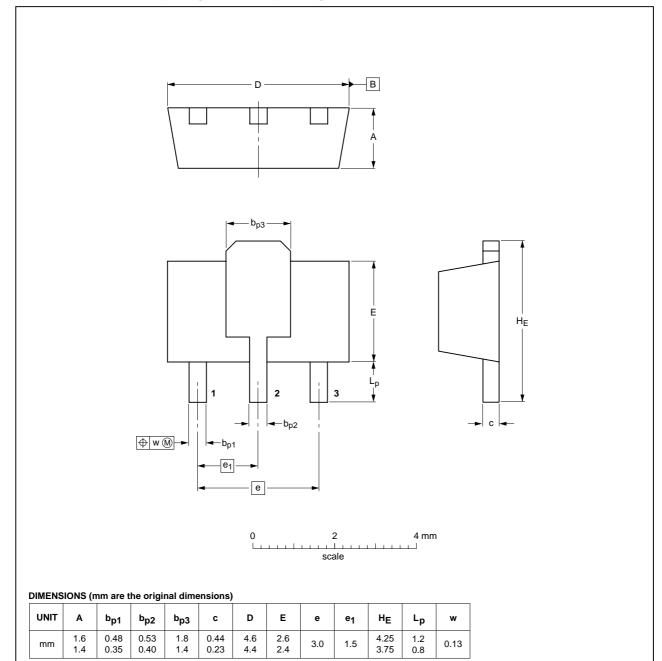
# PNP Darlington transistors

BST60; BST61; BST62

### **PACKAGE OUTLINE**

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE	E REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT89		TO-243	SC-62			<del>04-08-03</del> 06-03-16

### PNP Darlington transistors

BST60; BST61; BST62

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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### **Contact information**

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